METHOD OF FORMING A SEAL FOR A SEMICONDUCTOR DEVICE

Abstract of the Disclosure

In one embodiment, a reflowable layer 51 is deposited over a semiconductor device 10 and reflowed in an environment having a pressure approximately equal to that of atmosphere to form a seal layer 52. The seal layer 52 seals all openings 43 in the underlying layer of the semiconductor device 10. Since the reflow is performed at approximately atmospheric pressure a gap 50 which was coupled to the opening 43 is sealed at approximately atmospheric pressure, which is desirable for the semiconductor device 10 to avoid oscillation. The seal layer 52 is also desirable because it prevents particles from entering the gap 50. In another embodiment, the seal layer 52 is deposited in an environment having a pressure approximately equal to atmospheric pressure to seal the hole 43 without a reflow being performed.

(FIGs. 12 and 13 to accompany abstract)